

#### **Features**

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(ON)</sub>
- Halogen Free. "Green" Device (1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- · Moisture Sensitivity Level 3

## **Maximum Ratings**

Operating Junction Temperature Range : -55°C to +150°C

• Storage Temperature Range: -55°C to +150°C

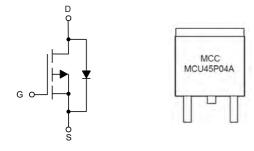
• Thermal Resistance: 1.9°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	-40	V
Gate-Source Volltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	-45	Α
Pulsed Drain Current <sup>(2)</sup>	I <sub>DM</sub>	-160	Α
Total Power Dissipation <sup>(3)</sup>	P <sub>D</sub>	65	W
Single Pulsed Avalanche Energy <sup>(4)</sup>	E <sub>AS</sub>	132	mJ

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

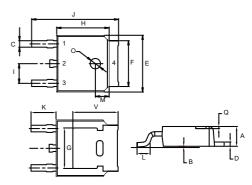
- 2.petitive rating; pulse width limited by max. junction temperature.
- 3.PD is based on max. junction temperature, using junction-case thermal resistanc.
- 4.VDD=-30V, VGS=-10V, L=0.5mH, IAS=23A.

## **Internal Structure and Marking Code**



# P-CHANNEL MOSFET

# **DPAK(TO-252)**



- 1. Gate
- 2,4. Drain
  - 3. Source

DIMENSIONS					
DIM INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
Е	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
ı	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
М	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.3	35	TYP.

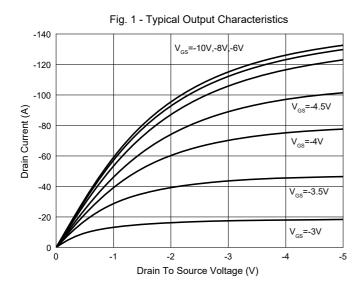


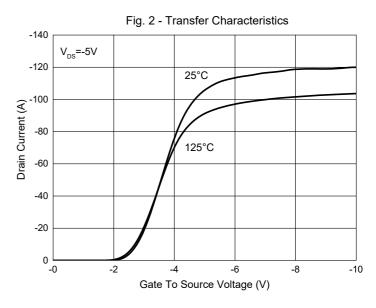
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

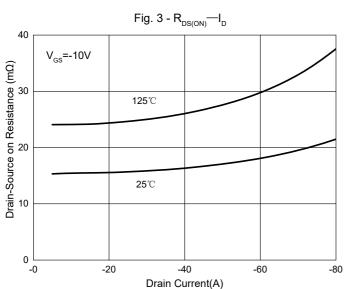
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics				1			
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-40			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V			-1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.6	-2.5	V	
Drain Cauras On Basistanas	_	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A		15	20	mΩ	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A		19	23		
Gate Resistance	$R_g$	f=1MHz, Open drain		10		Ω	
Diode Characteristics					1		
Continuous Body Diode Current	Is				-45	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-20A			-1.3	V	
Reverse Recovery Time	t <sub>rr</sub>	1 004 11 / 1/ 4004 /		22		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> =-20A, dI <sub>F</sub> /dt=100A/μs		8.8		nC	
Dynamic Characteristics					1		
Input Capacitance	C <sub>iss</sub>			2539			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V,f=1MHz		194		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			187		1	
Total Gate Charge	Qg			57.1			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-20A		11.27		nC	
Gate-Drain Charge	$Q_{gd}$			11.5			
Turn-On Delay Time	t <sub>d(on)</sub>			7.7			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =-20V, V <sub>GEN</sub> =-10V,		47.8			
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G=3\Omega$ , $I_{DS}=-20A$		109.7		ns	
Turn-Off Fall Time	t <sub>f</sub>			68.6			

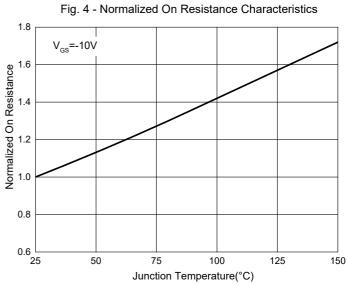


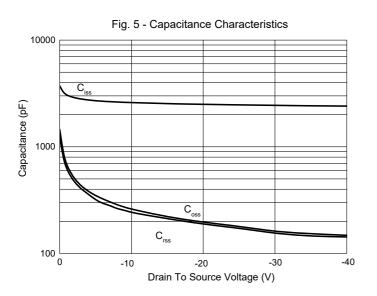
#### **Curve Characteristics**

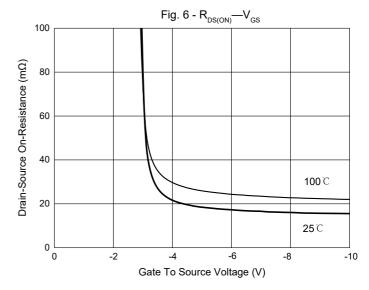






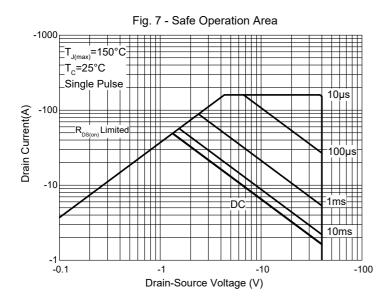


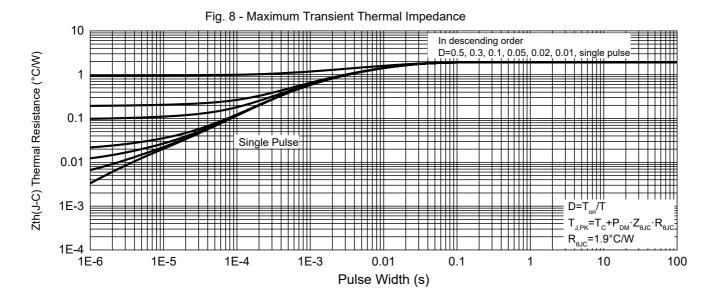






#### **Curve Characteristics**







## **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel	

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